



Docket No.: 251598US0



COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

RE: Application Serial No.: 10/820,123

Applicants: Yukio HOSAKA, et al.

Filing Date: April 8, 2004

For: ABRASIVE PAD, METHOD AND METAL MOLD  
FOR MANUFACTURING THE SAME, AND  
SEMICONDUCTOR WAFER POLISHING METHOD

Group Art Unit: 3723

Examiner: RACHUBA, MAURINA T.

SIR:

Attached hereto for filing are the following papers:

**Response to Restriction Requirement (3 pp.)**

Our check in the amount of **0.00** is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R. 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 15-0030. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. 1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

YUKIO HOSAKA, ET AL.

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RESPONSE TO RESTRICTION REQUIREMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

This is responsive to the Restriction Requirement mailed March 20, 2006.

Applicants elect, with traverse, the claims of Group I, Claims 1-6, 10 and 11, for examination.

Applicants further elect as a species for examination purposes only, species 1, Figs. 1-8.

Claims 1-6, 10 and 11 are readable on the elected species.

**Remarks/Arguments** begin on page 2 of this paper.